

产品规格书

Specification of products

产品名称: 三相全控桥

产品型号: MDST100A-H3

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

地址: 浙江省 丽水市 莲都区

电话: (0578) 3012571 3615078

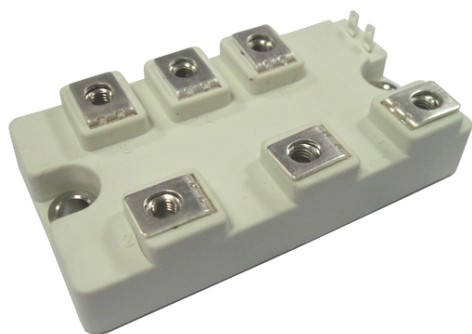
传真: (0578) 3611180

邮编: 323000

E-mail: smrshiling01@163.com

Http://www.smrshiling.com

拟制	审核	核准
林益龙	曹剑龙	宗瑞



Three Phase Bridge + Thyristor

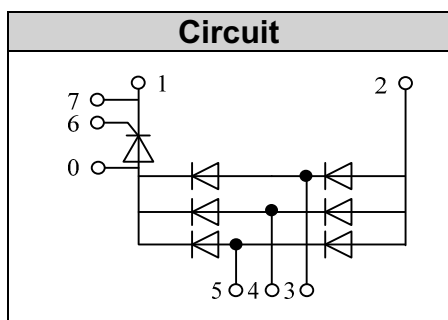
V_{RRM} / V_{DRM} 800 to 1800V
 I_{FAV} / I_{TAV} 100A

Features

- Blocking voltage:800 to 1800V
- Three Phase Bridge and a Thyristor
- Isolated Module package

Applications

- Inverter for AC or DC motor control
- Current stabilized power supply
- Switching power supply



Module Type

TYPE	V_{RRM} / V_{DRM}	V_{RSM}
MDST100A800V	800V	900V
MDST100A1200V	1200V	1300V
MDST100A1600V	1600V	1700V
MDST100A1800V	1800V	1900V

◆ Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_D	Output Current(D.C.)	$T_c=100^\circ\text{C}$ Three phase full wave	100	A
I_{FSM}	Surge forward current	$t=10\text{mS}$ $T_{vj}=45^\circ\text{C}$	1200	A
i^2t	Circuit Fusing Consideration		7200	A^2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T_{vj}	Operating Junction Temperature		-40 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40 to +125	$^\circ\text{C}$
M_t	Mounting Torque	To terminals(M5)	$3 \pm 5\%$	Nm
M_s		To heatsink(M5)	$3 \pm 5\%$	Nm
Weight		Module (Approximately)	210	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case(TOTAL)	0.18	$^\circ\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal Impedance, max.	Case to Heatsink	0.10	$^\circ\text{C}/\text{W}$

Electrical Characteristics

Symbol	Item	Conditions	Values	Units
V_{FM}	Forward Voltage Drop, max.	$T=25^\circ\text{C}$ $I_F=150\text{A}$	1.30	V
I_{RRM}	Repetitive Peak Reverse Current, max.	$T_{vj}=25^\circ\text{C}$ $V_{RD}=V_{RRM}$ $T_{vj}=150^\circ\text{C}$ $V_{RD}=V_{RRM}$	≤ 0.5 ≤ 6	mA mA

◆Thyristor

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_{TAV}	Average On-State Current	$T_c=92^{\circ}\text{C}$, Single Phase half wave 180° conduction	100	A
I_{TSM}	Surge On-State Current	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $V_R=0$	1200	A
i^2t	Circuit Fusing Consideration		7200	A^2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50Hz;r.m.s.;1 min	3000	V
T_{vj}	Operating Junction Temperature		-40 to +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-40 to +125	$^{\circ}\text{C}$
M_t	Mounting Torque	To terminals(M5)	$3 \pm 5\%$	Nm
M_s		To heatsink(M5)	$3 \pm 5\%$	Nm
di/dt	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$, $V_D=1/2V_{DRM}$, $I_G=100\text{mA}$ $d_{iG}/d_t=0.1\text{A}/\mu\text{s}$	150	$\text{A}/\mu\text{s}$
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$, $V_D=2/3V_{DRM}$, linear voltage rise	500	$\text{V}/\mu\text{s}$

Electrical and Thermal Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V_{TM}	Peak On-State Voltage, max.	$T=25^{\circ}\text{C}$ $I_T=150\text{A}$		1.35	V	
I_{RRM}/I_{DRM}	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	$T_{VJ}=T_{VJM}$, $V_R=V_{RRM}$, $V_D=V_{DRM}$		20	mA	
V_{GT}	Gate Trigger Voltage, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$		3	V	
I_{GT}	Gate Trigger Current, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$		150	mA	
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case			0.26	$^{\circ}\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal Impedance, max.	Case to Heatsink			0.10	$^{\circ}\text{C}/\text{W}$

Performance Curves

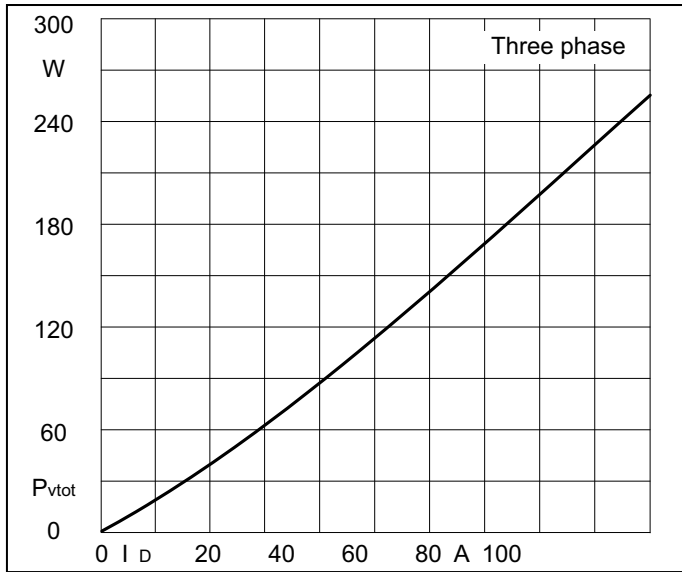


Fig1. Power dissipation

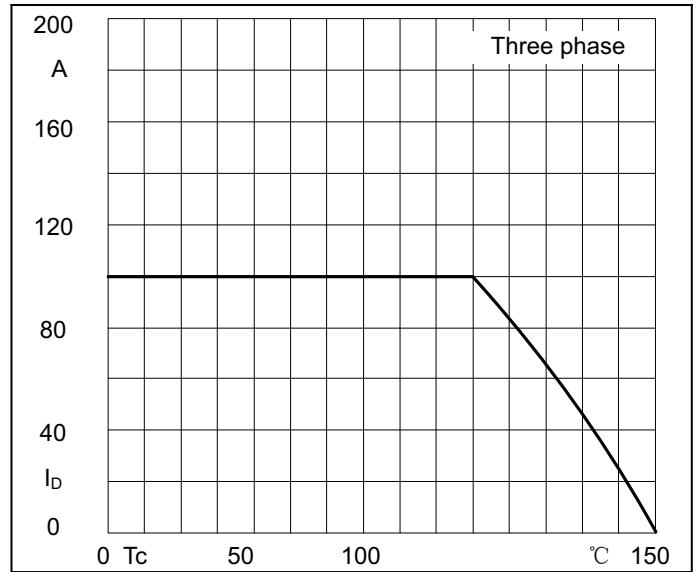


Fig2. Forward Current Derating Curve

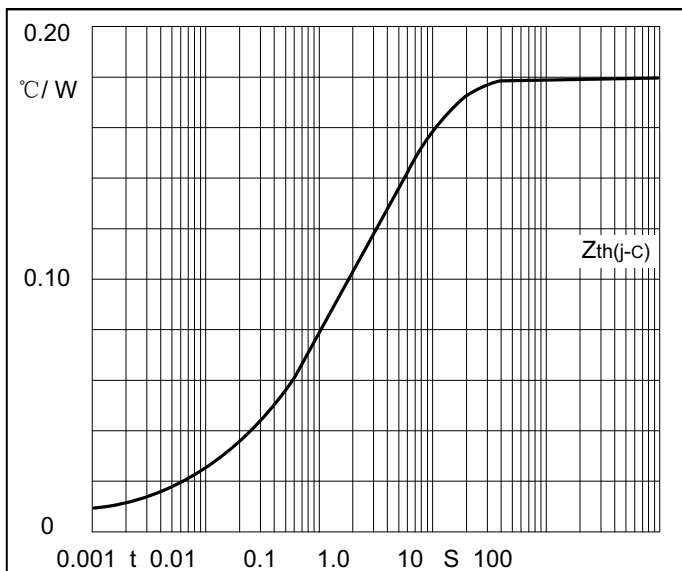


Fig3. Transient thermal impedance

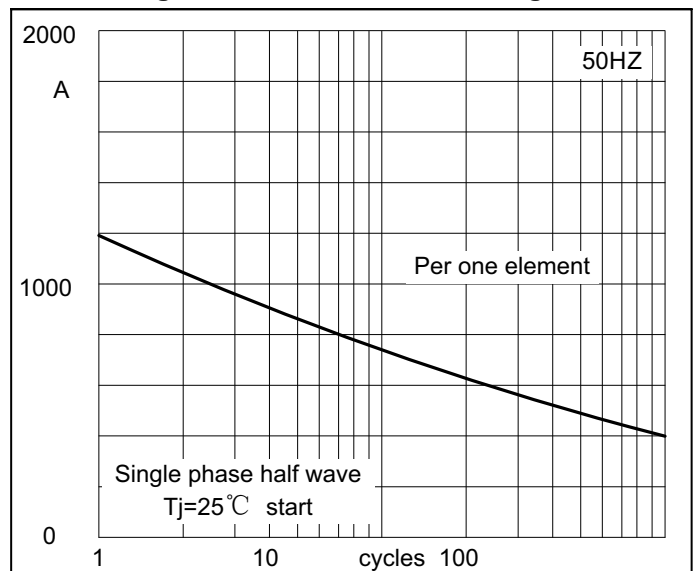


Fig4. Max Non-Repetitive Forward Surge Current

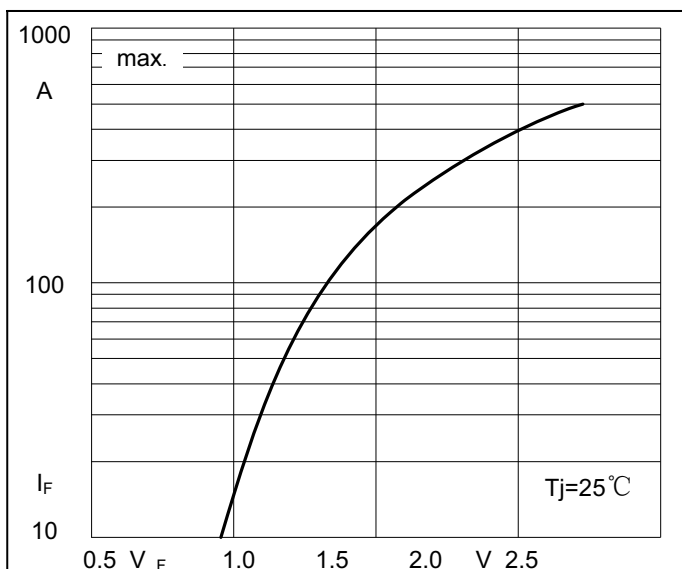


Fig5. Forward Characteristics

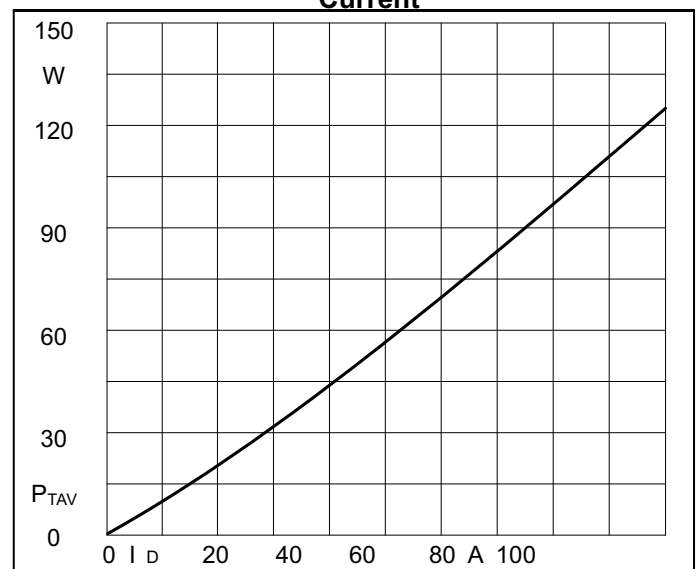


Fig6. SCR Power dissipation

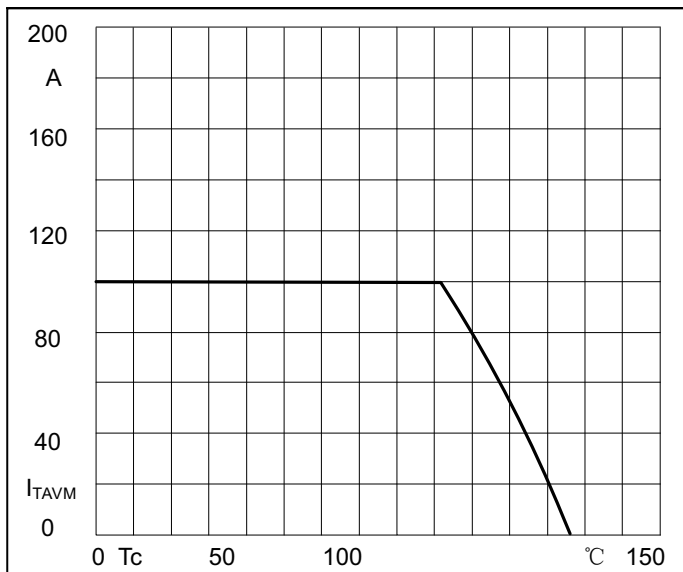


Fig7. SCR Forward Current Derating Curve

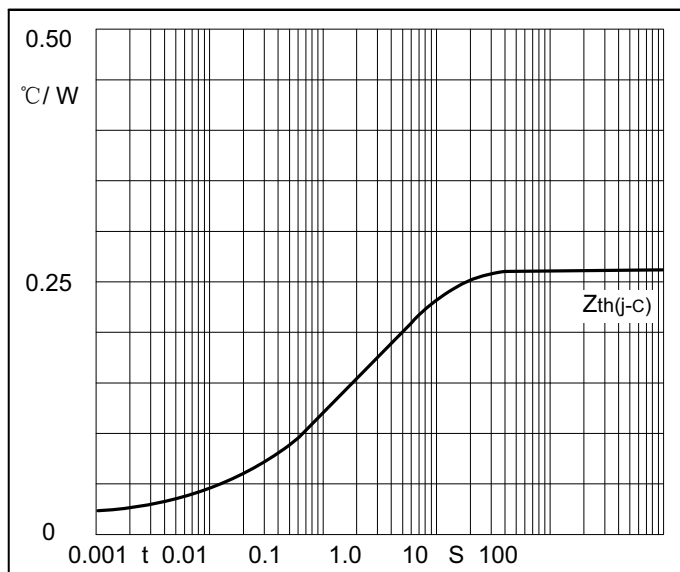


Fig8. SCR Transient thermal impedance

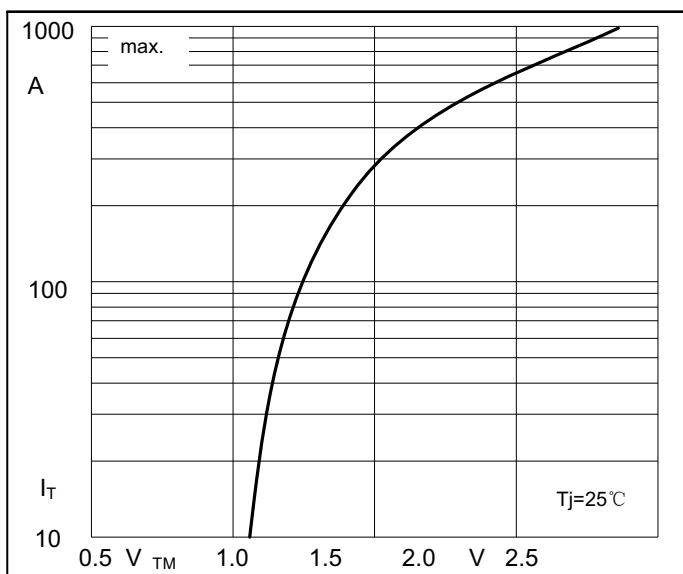


Fig9. SCR Forward Characteristics

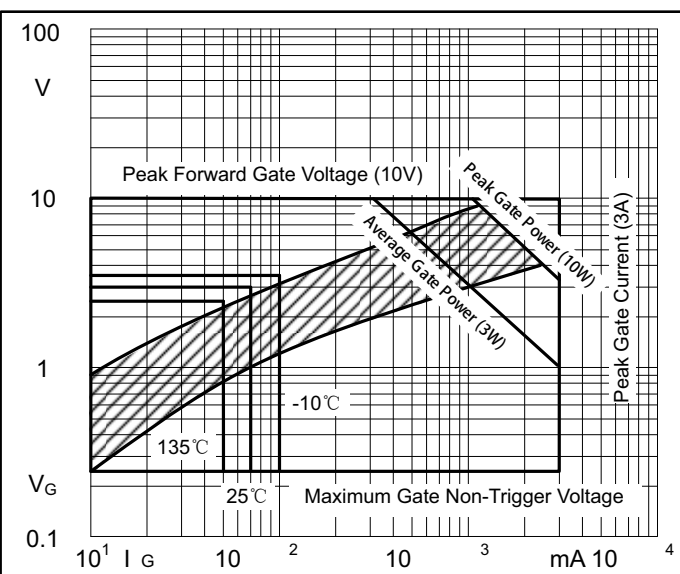


Fig10. Gate trigger Characteristics

Package Outline Information

